

Complementary Bias Resistor Transistors R1 = 2.2 k Ω , R2 = ∞ k Ω NSBC123TPDP6

NPN and PNP Transistors with Monolithic Bias Resistor Network

This series of digital transistors is designed to replace a single device and its external resistor bias network. The Bias Resistor Transistor (BRT) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base–emitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space.

Features

- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

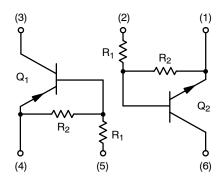
 $(T_A = 25^{\circ}C \text{ both polarities Q1 (PNP) and Q2 (NPN), unless otherwise noted)}$

Rating	Symbol	Max	Unit
Collector-Base Voltage	V_{CBO}	50	Vdc
Collector-Emitter Voltage	V_{CEO}	50	Vdc
Collector Current – Continuous	I _C	100	mAdc
Input Forward Voltage	$V_{IN(fwd)}$	12	Vdc
Input Reverse Voltage -NPN -PNP	V _{IN(rev)}	6 5	Vdc

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1

PIN CONNECTIONS



MARKING DIAGRAMS





SOT-963 CASE 527AD

A = Specific Device Code M = Date Code*

*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
NSBC123TPDP6T5G	SOT-963	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
NSBC123TPDP6 (SOT-963) One Junction Heated	•	•	•
Total Device Dissipation T _A = 25°C (Note 1) (Note 2) Derate above 25°C (Note 1) (Note 2)	P _D	231 269 1.9 2.2	mW mW/°C
Thermal Resistance, (Note 1) Junction to Ambient (Note 2)	$R_{ hetaJA}$	540 464	°C/W
NSBC123TPDP6 (SOT-963) Both Junction Heated (Note 3)		•	
Total Device Dissipation T _A = 25°C (Note 1) (Note 2) Derate above 25°C (Note 1) (Note 2)	P _D	339 408 2.7 3.3	mW mW/°C
Thermal Resistance, (Note 1) Junction to Ambient (Note 2)	$R_{ hetaJA}$	369 306	°C/W
Junction and Storage Temperature Range	T _J , T _{stq}	-55 to +150	°C

FR-4 @ 100 mm², 1 oz. copper traces, still air.
 FR-4 @ 500 mm², 1 oz. copper traces, still air.
 Both junction heated values assume total power is sum of two equally powered channels.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ both polarities Q_1 (PNP) and Q_2 (NPN), unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS			•	•	
Collector-Base Cutoff Current (V _{CB} = 50 V, I _E = 0)	I _{CBO}	_	-	100	nAdc
Collector-Emitter Cutoff Current (V _{CE} = 50 V, I _B = 0)	I _{CEO}	_	_	500	nAdc
Emitter–Base Cutoff Current $(V_{EB} = 6.0 \text{ V}, I_{C} = 0)$	I _{EBO}	-	_	4.0	mAdc
Collector–Base Breakdown Voltage ($I_C = 10 \mu A, I_E = 0$)	V _(BR) CBO	50	_	-	Vdc
Collector-Emitter Breakdown Voltage (Note 4) (I _C = 2.0 mA, I _B = 0)	V _(BR) CEO	50	-	-	Vdc
ON CHARACTERISTICS	•		•	•	
DC Current Gain (Note 4) (I _C = 5.0 mA, V _{CE} = 10 V)	h _{FE}	160	350	_	
Collector-Emitter Saturation Voltage (Note 4) (I _C = 10 mA, I _B = 1.0 mA)	V _{CE(sat)}	-	_	0.25	Vdc
Input Voltage (off) ($V_{CE} = 5.0 \text{ V}, I_{C} = 100 \mu\text{A}$) (NPN) ($V_{CE} = 5.0 \text{ V}, I_{C} = 100 \mu\text{A}$) (PNP)	V _{i(off)}	- -	0.6 0.6	- -	Vdc
Input Voltage (on) $(V_{CE} = 0.2 \text{ V, } I_{C} = 10 \text{ mA}) \text{ (NPN)} $ $(V_{CE} = 0.2 \text{ V, } I_{C} = 10 \text{ mA}) \text{ (PNP)}$	V _{i(on)}	- -	0.9 0.9	- -	Vdc
Output Voltage (on) $(V_{CC} = 5.0 \text{ V}, V_B = 2.5 \text{ V}, R_L = 1.0 \text{ k}\Omega)$	V _{OL}	_	_	0.2	Vdc
Output Voltage (off) $(V_{CC} = 5.0 \text{ V}, V_B = 0.25 \text{ V}, R_L = 1.0 \text{ k}\Omega)$	V _{OH}	4.9	_	-	Vdc
Input Resistor	R1	1.5	2.2	2.9	kΩ
Resistor Ratio	R ₁ /R ₂	-	-	-	

^{4.} Pulsed Condition: Pulse Width = 300 msec, Duty Cycle ≤ 2%.

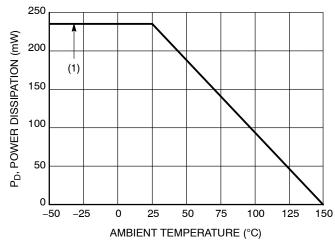
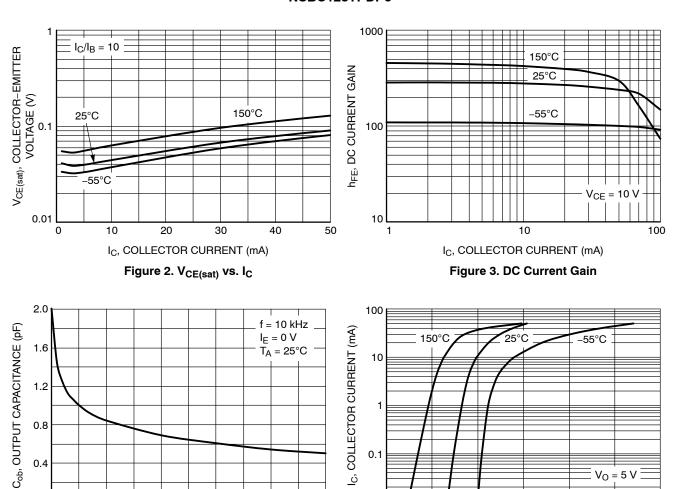


Figure 1. Derating Curve

(1) SOT-963; 100 mm², 1 oz. copper trace

TYPICAL CHARACTERISTICS – NPN TRANSISTOR NSBC123TPDP6



 V_R , REVERSE VOLTAGE (V) Figure 4. Output Capacitance

0

10

 $\label{eq:Vin} V_{in}, \text{INPUT VOLTAGE (V)}$ Figure 5. Output Current vs. Input Voltage

2.4

0.4

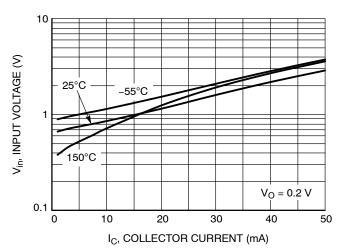


Figure 6. Input Voltage vs. Output Current

TYPICAL CHARACTERISTICS – PNP TRANSISTOR NSBC123TPDP6

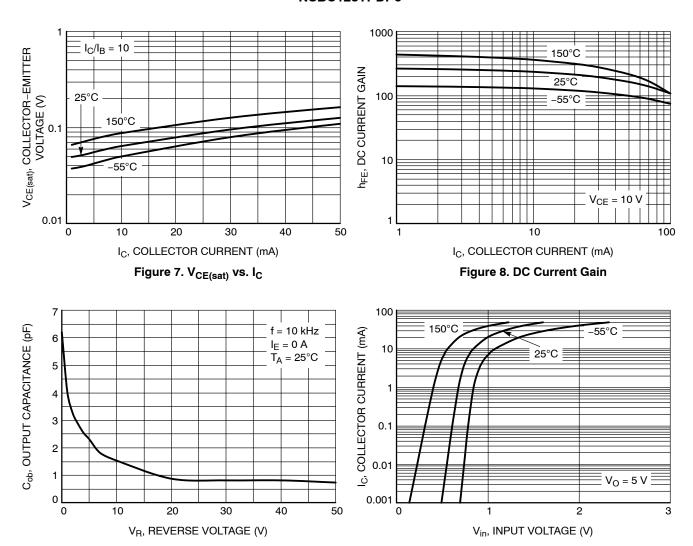


Figure 9. Output Capacitance

Figure 10. Output Current vs. Input Voltage

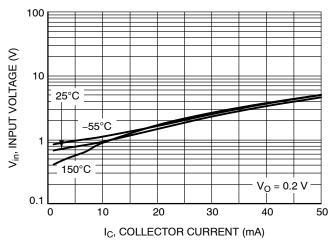


Figure 11. Input Voltage vs. Output Current





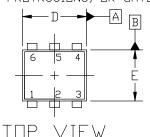


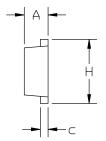
SOT-963 1.00x1.00x0.37, 0.35P CASE 527AD **ISSUE F**

DATE 20 FEB 2024

NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018. 1.
- CONTROLLING DIMENSION: MILLIMETERS.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS, MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
 DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH,
- PROTRUSIONS, OR GATE BURRS

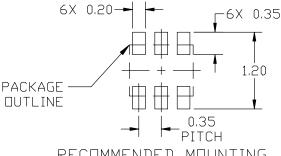




VIFW



	MILLIMETERS		
DIM	MIN.	N□M.	MAX.
А	0.34	0.37	0.40
b	0.10	0.15	0.20
C	0.07	0.12	0.17
D	0.95	1.00	1.05
E	0.75	0.80	0.85
е	0.35 BSC		
Н	0.95	1.00	1.05
L	0.19 REF		
L2	0.05	0.10	0.15



RECOMMENDED MOUNTING FOOTPRINT

*For additional information on our Pb-Free strategy and soldering details, please download the $\ensuremath{\square N}$ Semiconductor Soldering and Mounting Techniques Reference manual, SOLDERRM/D.

BUTTUM VIEW

STYLE 1:	STYLE 2:	STYLE 3:
PIN 1. EMITTER 1	PIN 1. EMITTER 1	PIN 1. CATHODE 1
2. BASE 1	EMITTER2	CATHODE 1
COLLECTOR 2	3. BASE 2	ANODE/ANODE 2
4. EMITTER 2	COLLECTOR 2	CATHODE 2
5. BASE 2	5. BASE 1	CATHODE 2
COLLECTOR 1	COLLECTOR 1	6. ANODE/ANODE 1
STYLE 4:	STYLE 5:	STYLE 6:

PIN 1. CATHODE 2. CATHODE 3. ANODE 4. ANODE PIN 1. COLLECTOR 2. COLLECTOR 3. BASE 4. EMITTER

PIN 1. CATHODE 2. ANODE 3. CATHODE 4. CATHODE 5 CATHODE CATHODE 6. CATHODE 6. CATHODE

5. COLLECTOR 6. COLLECTOR STYLE 8: PIN 1. DRAIN 2. DRAIN STYLE 7: PIN 1. CATHODE 2. ANODE 3. CATHODE 4. CATHODE 3. GATE 4. SOURCE 5. ANODE 6. CATHODE 5. DRAIN 6. DRAIN 5. GATE 2 6. DRAIN 1

STYLE 9: PIN 1. SOURCE 1 2. GATE 1 3. DRAIN 2 4. SOURCE 2

GENERIC MARKING DIAGRAM*



XX = Specific Device Code = Month Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "=", may or may not be present. Some products may not follow the Generic Marking.

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DESCRIPTION:	SOT-963 1.00x1.00x0.37, 0.35P		PAGE 1 OF 1

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STYLE 10: PIN 1. CATHODE 1 2. N/C 3. CATHODE 2

4. ANODE 2

5. N/C 6. ANODE 1

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